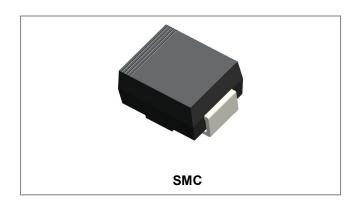






SK32 THRU SK310 SCHOTTKY RECTIFIER



Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inventers, Free Wheeling, and Polarity Protection Applications
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: Low Profile Molded plastic
- Terminals: Plated leads solderable per MIL-STD-750,
 Makked 2026 supported.
- Method 2026 guaranteed
- Polarity: Color band or cathode Notch
- Mounting Position: Any
- Weight: 0.21grams(approx)

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Characteristic	Symbol	SK32	SK33	SK34	SK35	SK36	SK38	SK39	SK310	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	20	30	40	50	60	80	90	100	V
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	56	64	71	V
Average Rectified Output Current @T _L = 75°C	Io	3.0				Α				
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	100				Α				
Forward Voltage @ I _F = 3.0 A	V _F		0.55		0	.75		0.85		V
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _{RM}	0.5 20				mA				
Typical Thermal Resistance Junction to Ambient (Note 1)	R _{θJA}	55			°C/W					
Operating Temperature Range	TJ	-65 to +125			°C					
Storage Temperature Range	T _{STG}	-65 to +150			°C					

Note: 1. mounted on P.C. Board with 8.0mm^2 copper pad areas.

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Ratings and Characteristics Curves

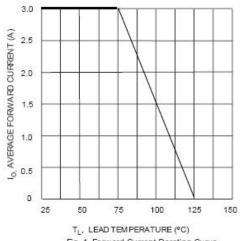


Fig. 1 Forward Current Derating Curve

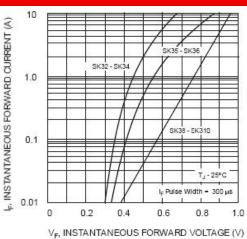
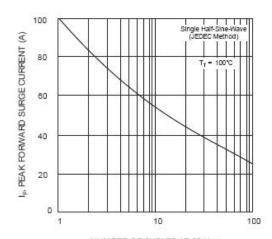
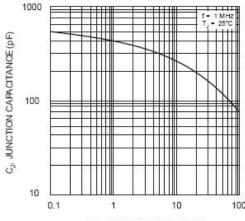


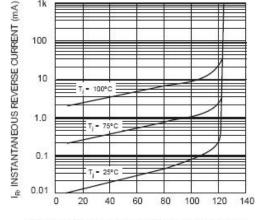
Fig. 2 Typical Forward Characteristics



NUMBER OF CYCLES AT 60 Hz Fi . 3 Max Non-Repetitive Peak Fwd Sur e Current



V_R, REVERSE VOLTAGE (V) Fig. 4 Typical Junction Capacitance



PERCENT OF RATED PEAK REVERSE VOLTAGE (%) Fig. 5. Typical Reverse Characteristics

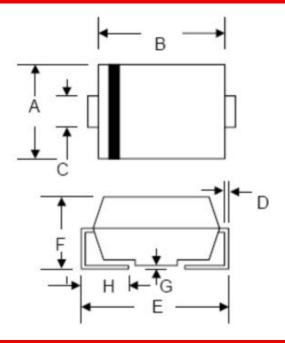
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Mechanical Dimensions SMC



CYMPOL	Millin	neters	Inches			
SYMBOL	Min.	Max.	Min.	Max.		
Α	5.59	6.22	0.220	0.245		
В	6.60	7.11	0.260	0.280		
С	2.75	3.25	0.108	0.128		
D	0.152	0.305	0.006	0.012		
E	7.75	8.25	0.305	0.325		
F	2.00	2.95	0.079	0.116		
G	0.051	0.203	0.002	0.008		
Н	0.76	1.60	0.030	0.063		

Ordering Information

Device	Package	Shipping			
SK32					
THRU	SMC (Pb-Free)	3000pcs / reel			
SK310					

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

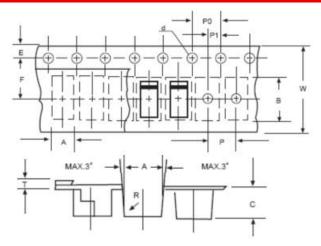
Marking Diagram



Where XXXXX is YYWWL

First row: Part Number (SK32, SK33, SK34, SK35, SK36, SK38, SK39, SK310)
Second row: YYWWL
YY is the manufacture year,
WW is the manufacture week code,
L is the wafer's Lot Number

Carrier Tape Specification SMC



SYMBOL	Millimeters				
STIVIBUL	Min.	Max.			
Α	5.90	6.10			
В	8.20	8.40			
С	2.40	2.60			
d	1.40	1.60			
Е	1.40	1.60			
F	7.60	7.70			
Р	7.90	8.10			
P0	3.90	4.10			
P1	3.90	4.10			
Т	-	0.600			
W	15.80	16.20			

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